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[Signature] Karen Cinq-Mars 10/10/03
(signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of _____ : October 10, 2003
Chen, et al. _____ : Group Art Unit:
Serial No. 10/605,134 : Examiner:
Filed: 9/10/03 : International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: STRUCTURE AND METHOD OF MAKING STRAINED CHANNEL CMOS TRANSISTORS
HAVING LATTICE-MISMATCHED EPITAXIAL EXTENSION AND SOURCE AND DRAIN
REGIONS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.


In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
Chen, et al.

By [Signature]
H. Daniel Schnurmann
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FIS920030198US1

FORM PTO-1449 (Modified)				ATTY. DOCKET NO. FIS920030198US1	SERIAL NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT				APPLICANT: CHEN ET AL.	
(Use several sheets if necessary)				FILING DATE:	GROUP:

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	ISSUED DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ							

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

	AN	Nayak, Deepak K. et al.; "High-Mobility Strained-Si PMOSFET'S," <u>IEEE Transactions On Electron Devices</u> , Vol. 43, No. 10, October 1996, pages 1709-1716.
	AO	
	AP	
	AQ	
	AR	

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.